Transmissive Optical Sensor with Phototransistor Output

Description

These devices have a compact construction where the emitting light sources and the detectors are located face to face on the same optical axis. The operating wavelength is 950 nm. The detector consists of a phototransistor. As a result of special construction the depth of the gap is equal to package height of 4.0 mm.



Applications

- Position sensor for shaft encoder
- Detection of opaque material like paper, IBM cards, magnetic tapes etc.
- Limit switch for mechanical motions in VCR
- General purpose where ever the space is limited

Features

- Gap 2.8 mm
- Different package height: TCST5123: 4.0 mm TCST5133: 16.0 mm

- Plastic polycarbonate housing
- Subminiature construction
- Snap in mounting mechanisms

Pin Connection

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Absolute Maximum Ratings

Input (Emitter)

Parameters	Test Conditions	Symbol	Value	Unit
Reverse voltage		V_{R}	6	V
Forward current		I_{F}	60	mA
Forward surge current	$t_p \le 10 \ \mu s$	I _{FSM}	3	A
Power dissipation	$T_{amb} \le 25^{\circ}C$	P_{v}	100	mW
Junction temperature		T _i	100	°C

Output (Detector)

Parameters	Test Conditions	Symbol	Value	Unit
Collector emitter voltage		V_{CEO}	70	V
Emitter collector voltage		V _{ECO}	7	V
Collector current		I_{C}	100	mA
Power dissipation	$T_{amb} \le 25^{\circ}C$	P_{v}	150	mW
Junction temperature		Ti	100	°C

Coupler

Parameters	Test Conditions	Symbol	Value	Unit
Total power dissipation	$T_{amb} \le 25^{\circ}C$	P _{tot}	250	mW
Operation temperature range		T _{amb}	-25 to +85	°C
Storage temperature range		T _{stg}	-55 to +100	°C
Soldering temperature	t ≤ 3 s	T _{sd}	260	°C
	distance 1.5 mm from case			

Electrical Characteristics $T_{amb} = 25^{\circ}C$

Input (Emitter)

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Forward voltage	$I_F = 60 \text{ mA}$	V_{F}		1.25	1.5	V
Breakdown voltage	$I_R = 100 \mu A$	V _(BR)	6			V
Junction capacitance	$V_R = 0$, $f = 1$ MHz	Cj		50		pF

Output (Detector)

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Collector emitter voltage	$I_C = 1 \text{ mA}$	V_{CEO}	70			V
Emitter collector voltage	$I_E = 100 \mu A$	V _{ECO}	7			V
Collector dark current	$V_{CE} = 25 \text{ V}, I_F = 0,$ E = 0	I _{CEO}			100	nA

Coupler

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Collector current 1)	$V_{CE} = 5 \text{ V}, I_F = 20 \text{ mA}$	I _C	2.4		7.2	mA
Crosstalk 2)	$V_{CE} = 5 \text{ V}, I_F = 20 \text{ mA}$	I_{CX}		50		μΑ
Collector emitter	$I_F = 20 \text{ mA},$	V _{CEsat}			0.4	V
saturation voltage	$I_{\rm C} = 0.025 \text{ mA}$					

¹⁾ without shield

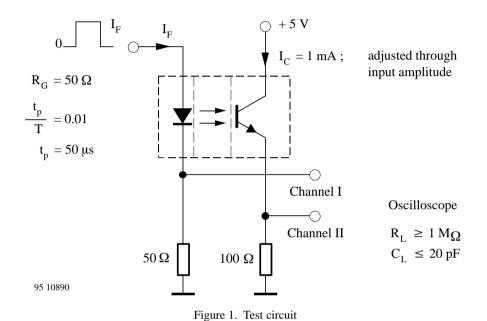
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²⁾ with shield, see mech. setup

Switching Characteristics

see test circuit

Parameters	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Turn-on time	$I_C = 1 \text{ mA},$	t _{on}		15		μs
Turn-off time	$V_{CE} = 5 \text{ V},$ $R_L = 100 \Omega$	$f_{ m off}$		10		μs



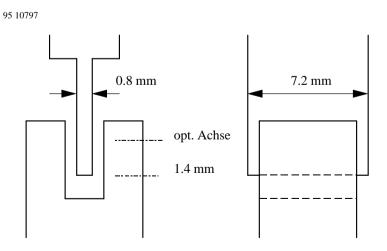


Figure 2. Mechanical setup

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Ozone Depleting Substances Policy Statement

It is the policy of TEMIC TELEFUNKEN microelectronic GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

TEMIC TELEFUNKEN microelectronic GmbH semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

TEMIC can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use TEMIC products for any unintended or unauthorized application, the buyer shall indemnify TEMIC against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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